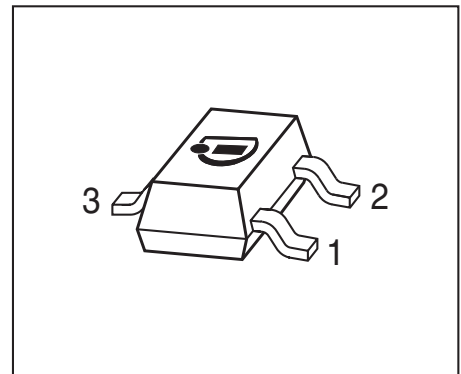


## NPN Bipolar RF Transistor

- For low noise, high-gain amplifiers up to 2 GHz
- For linear broadband amplifiers
- $f_T = 8 \text{ GHz}$ ,  $NF_{\min} = 1 \text{ dB}$  at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BFR193	RCs	1 = B	2 = E	3 = C	SOT23

**Maximum Ratings** at  $T_A = 25 \text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	12	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	80	mA
Base current	$I_B$	10	
Total power dissipation <sup>1)</sup> $T_S \leq 69 \text{ °C}$	$P_{\text{tot}}$	580	mW
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{\text{Stg}}$	-55 ... 150	

## Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	$R_{\text{thJS}}$	140	K/W

<sup>1)</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2)</sup> For calculation of  $R_{\text{thJA}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

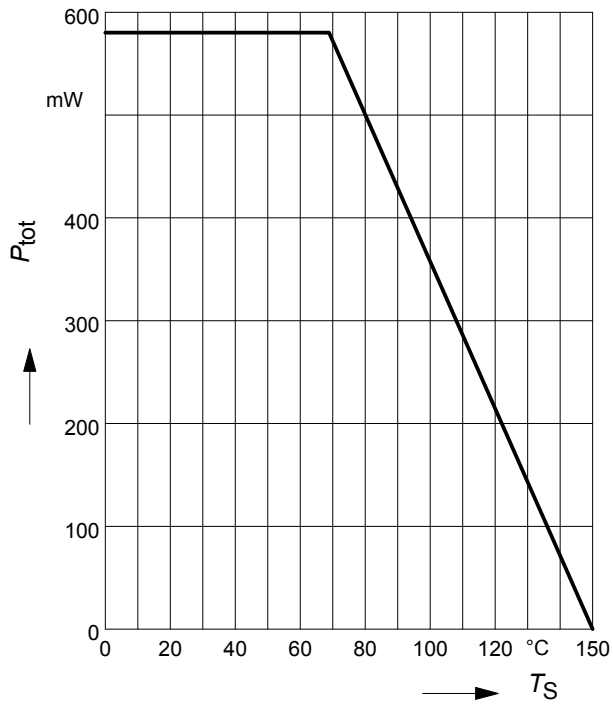
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$ , $I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$ , $V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10\text{ V}$ , $I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$ , $I_C = 0$	$I_{EBO}$	-	-	1	$\mu\text{A}$
DC current gain $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , pulse measured	$h_{FE}$	70	100	140	-

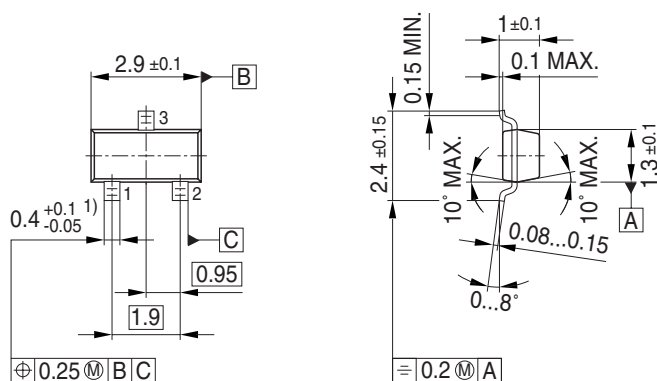
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b> (verified by random sampling)					
Transition frequency $I_C = 50\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.66	1	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.28	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	2.25	-	
Minimum noise figure $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900\text{ MHz}$ $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 1.8\text{ GHz}$	$NF_{min}$	- -	1 1.6	- -	dB
Power gain, maximum available <sup>1)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900\text{ MHz}$ $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$G_{ma}$	- -	15 10	- -	
Transducer gain $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900\text{ MHz}$ $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	- -	13 7.5	- -	

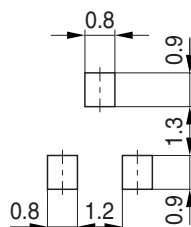
<sup>1)</sup>  $G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$

Total power dissipation  $P_{\text{tot}} = f(T_S)$



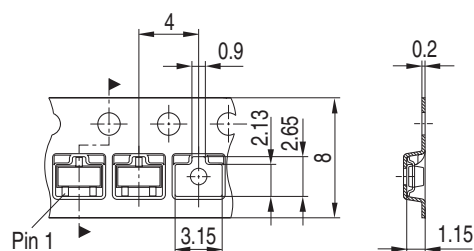


## Foot Print



The diagram shows a top-down view of a BCW66 LED package. It is a rectangular component with four pins. The top pin is labeled 'Pin 1'. The package has a central rectangular area containing the text 'EH S' and a date code '05 05'. The date code is split into two parts: '05' on the left and '05' on the right. The package is labeled with 'infineon' at the top, 'Manufacturer' below it, '2005, June' above the date code, 'Date code (YM)' below the date code, and 'BCW66' at the bottom, 'Type code' below it.

Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel



**Edition 2009-11-16**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

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